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ELECTRONIC HIGH FREQUENCY SWITCH AND ATTENUATOR WITH SAID
HIGH FREQUENCY SWITCHES

Abstract

5

In an electronic high-frequency switch, comprising a field-effect transistor as the switching element, the size of the gate voltage may be switched between at least two values (-5.5 V and -8 V), according to the desired linearity or 10 switching speed. The switching device for the gate voltage is preferably coupled to a correction device in which different correcting values for the different gate voltage values corresponding to different correcting values for transmission or reflection by the high frequency switch are 15 stored.